Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/709603	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:27
L2	38	(silicon adj nitride adj read adj only adj memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:04
L3	0	(silicon adj nitride adj read adj only adj memory) and plasma and treatment and test and inspection and wafer and quality and conrol and alloy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON.	2006/03/16 14:29
L4	1	(silicon adj nitride adj read adj only adj memory) and plasma and treatment and test	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:56
L5	1	(silicon adj nitride adj read adj only adj memory) and (plasma adj treatment)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:33
L6		(silicon adj nitride adj read adj only adj memory) and (plasma adj treat)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:33
L7	O	(silicon adj nitride adj read adj only adj memory) and (plasma adj treating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:33
L8	2	(silicon adj nitride adj read adj only adj memory)and plasma and test	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:35

L9	7	(silicon adj nitride adj read adj	US-PGPUB;	OR	ON	2006/03/16 14:36
		only adj memory)and plasma	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB			
L10	7	9 and (test or plasma or treat or treatment or etch or control or quality or inspection or alloy or allyoing or process or sort or cell or retention or capacity or heat or heating or baking or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:05
L11		(silicon adj nitride adj read adj only adj memory) and (cell adj retention adj capacity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:55
L12	0	(silicon adj nitride adj read adj only adj memory) and plasma and treat	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:56
L13	1	"6437398".PN.	USPAT; USOCR	OR	ON	2006/03/16 15:01
L14	4	(silicon adj nitride adj read adj only adj memory adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:05
L15	4	14 and (test or plasma or treat or treatment or etch or control or quality or inspection or alloy or allyoing or process or sort or cell or retention or capacity or heat or heating or baking or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
L16	513	438/9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
L17	3687	438/14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10

1/35 503 286	438/798 438/513 ("6869844").PN.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; ISOCR; EPO; JPO; DERWENT; IBM_TDB  USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR OR	ON	2006/03/16 15:11
503	438/798	USOCR; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	·		,
,		USOCR; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	OR .	ON	2006/03/16 15:11
1/35		USOCR; EPO; JPO; DERWENT;	<b>*</b> *.	•	
1700	438/723	US-PGPUB;	OR	ON	2006/03/16 15:11
1961	438/745	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR 	ON	2006/03/16 15:11
1519	438/381	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
2696	438/238	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
1590	438/264	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
		USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB			2006/03/16 15:10
	2696 1519	1590	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  US-PGPUB; US-PGPUB;	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  1590 438/264 US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  2696 438/238 US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  1519 438/381 US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  1961 438/745 US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  1961 438/745 US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  1735 438/723 US-PGPUB; OR	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  1590 438/264 US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  2696 438/238 US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  1519 438/381 US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB  1961 438/745 US-PGPUB; US-PGP

Page 3

L28	1	("6580630").PN.	USPAT	OR	OFF	2006/03/16 15:11
L29	1	("6469342").PN.	USPAT	OR	OFF	2006/03/16 15:12
L30	1	(memory adj cell adj retention adj check)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:18

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